

Product Overview

PCGA200T65NF8: IGBT, 650 V, 200 A Field Stop Trench

For complete documentation, see the data sheet.

PCGA200T65NF8

Features

- AEC-Q101 Qualified
- Max Junction Temperature 175°C
- Positive temperature Co-efficient
- Ease of Paralleling
- Short Circuit rated
- Very Low Saturation voltage: $V_{CE(SAT)} = 1.53V$ (Typ.) @ $I_C = 200A$
- Optimized for Motor Control Applications

Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	I_C Max (A)	$V_{GE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μ s)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Pack aged Diode	Package Type
PCGA200T65NF8	AEC Qualified PPAP Capable Pb-free Halide free	Active	650	-	1.53	-	-	-	-	-	229	5	-	-	No	

For more information please contact your local sales support at www.onsemi.com.

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